

*CLAIM AMENDMENTS*

1. (Currently Amended) A method ~~for~~ of manufacturing a buried wiring structure comprising:

depositing an insulating film on under-layer wiring;

forming a first depressed portion in ~~an~~ the insulating film;

applying a burying material to the first depressed portion and on said insulating film, filling the first depressed portion;

chemical mechanical polishing the burying material until the insulating film is exposed, leaving the burying material in the first depressed portion;

forming a resist having a pattern of a second depressed portion that overlaps the first depressed portion on the insulating film where the burying material is present;

etching the burying material and the insulating film, using the resist as a mask, to form the second depressed portion;

removing the resist and the burying material left after the etching; and

depositing an electrically conductive material in the first depressed portion and the second depressed portion.

Claims 2 and 3 (Cancelled)

4. (Currently Amended) The method ~~for~~ of manufacturing a buried wiring structure according to claim 21, including applying as the burying material an organic polymeric material having substantially the same etching rate as the insulating film.

5. (Currently Amended) The method ~~for~~ of manufacturing a buried wiring structure according to claim 1, including applying as the burying material an organic polymeric material containing no aromatic compounds.

6. (Currently Amended) The method ~~for~~ of manufacturing a buried wiring structure according to claim 5, further comprising forming an antireflective film on the insulating film before forming the resist.

7. (Currently Amended) The method ~~for~~ of manufacturing a buried wiring structure according to claim 6, wherein the burying material and the antireflective film are not soluble in each other.

In re Appln. of ISHIBASHI et al.  
Application No. 10/619,433

8. (New) The method of manufacturing a buried wiring structure according to claim 1, wherein the first depressed portion is a contact hole and the second depressed portion is a wiring channel, the contact hole being deeper and narrower than the wiring channel.

9. (New) The method of manufacturing a buried wiring structure according to claim 1, wherein the first depressed portion is a wiring channel and the second depressed portion is a contact hole, the contact hole being deeper and narrower than the wiring channel.